

## ABSTRACT OF THE DISCLOSURE

A semiconductor device includes an N channel MOS transistor. The N channel MOS transistor includes a first P type buried layer that isolates an N- epitaxial region formed on a P type substrate (P-SUB) from another N- epitaxial region, a drain formed in an N well in the N- epitaxial region, a source formed in a P well surrounding side faces of the N well so as to be separated from the N well, and a gate formed on each upper layer portion of the drain and the source. The MOS transistor also includes a second P type buried layer formed below the N well and the P well so as to be joined to the P well, and an N+ buried layer formed so as to be joined to the P type buried layer and the P-SUB. The N- epitaxial region, the P-SUB, and the first P type buried layer are connected to ground potential.